

N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
30	0.0028 at $V_{GS} = 10$ V	85 ^d	43nC
	0.0056 at $V_{GS} = 4.5$ V	75 ^d	

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

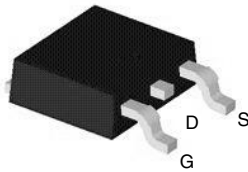


RoHS
COMPLIANT

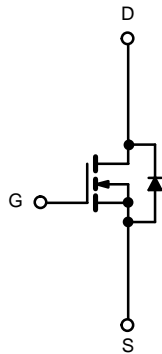
APPLICATIONS

- Power Supply
- Secondary Synchronous Rectification
- DC/DC Converter

TO-252 Pin Configuration



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	85 ^d
		$T_C = 70$ °C	70 ^d
Pulsed Drain Current	I_{DM}	210	A
Avalanche Current	I_{AS}	60	
Single Avalanche Energy ^a	E_{AS}	150	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C	92.8 ^b
		$T_A = 25$ °C ^c	4.1
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) ^c	R_{thJA}	26	°C/W
Junction-to-Case (Drain)	R_{thJC}	1.5	

Notes:

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).
- Package limited.

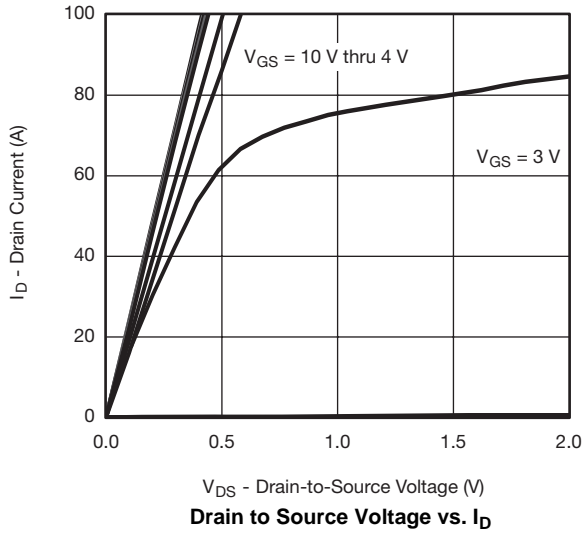
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$			250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$	50			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 22\text{ A}$		0.0028	0.0035	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$		0.0056	0.0061	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		130		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 15\text{ V}, f = 1\text{ MHz}$		2880		μF
Output Capacitance	C_{oss}			652		
Reverse Transfer Capacitance	C_{rss}			260		
Total Gate Charge ^c	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		43	66	nC
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		21.7	32.6	
Q_{gs}			7			
Q_{gd}			6.7			
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.4	2	4	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		8	16	ns
Rise Time ^c	t_r			9	18	
Turn-Off Delay Time ^c	$t_{d(off)}$			35	54	
Fall Time ^c	t_f			9	18	
Drain-Source Body Diode Ratings and Characteristics $T_C = 25\text{ }^\circ\text{C}$ ^b						
Continuous Current	I_S				85	A
Pulsed Current	I_{SM}				210	
Forward Voltage ^a	V_{SD}	$I_F = 10\text{ A}, V_{GS} = 0\text{ V}$		0.65	1.5	V
Reverse Recovery Time	t_{rr}	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		34	51	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			2	3	A
Reverse Recovery Charge	Q_{rr}			34	51	nC

Notes:

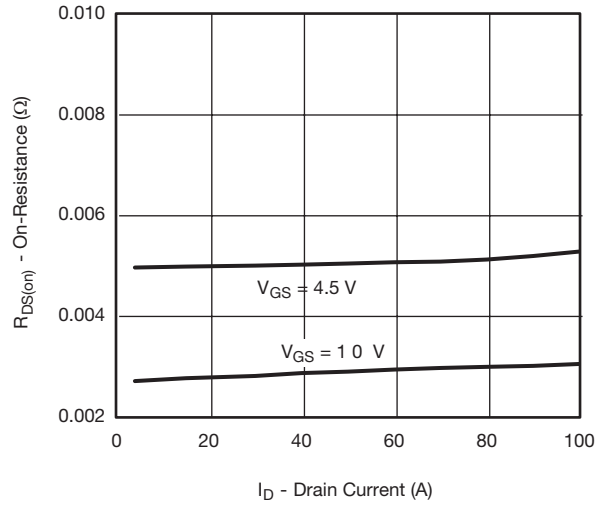
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

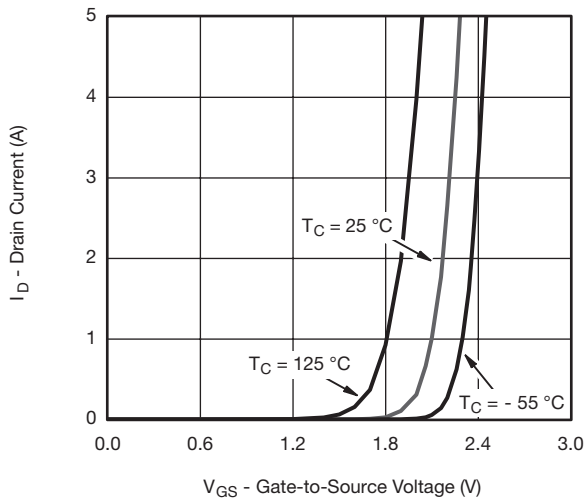
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



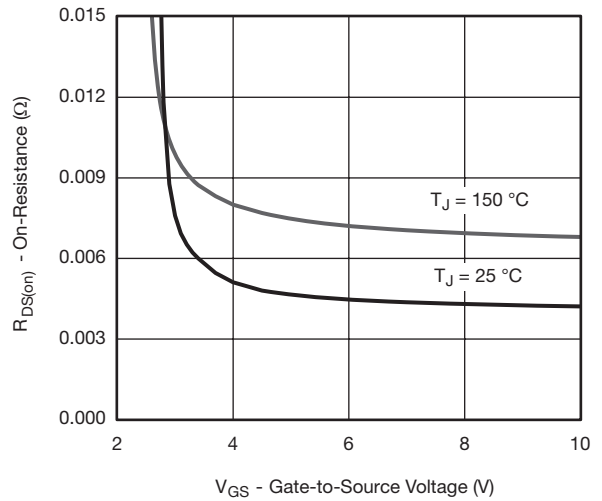
Drain to Source Voltage vs. I_D



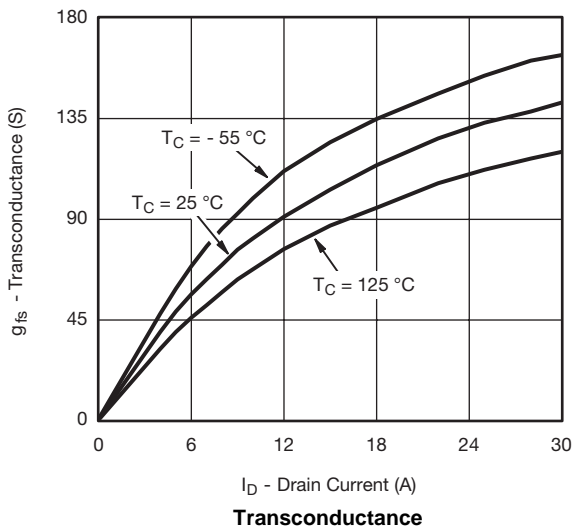
On-Resistance vs. Drain Current



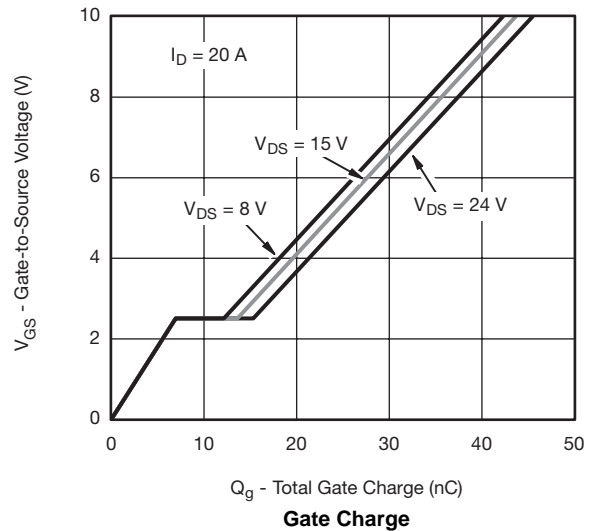
Transfer Characteristics



On-Resistance vs. Gate-to-Source Voltage

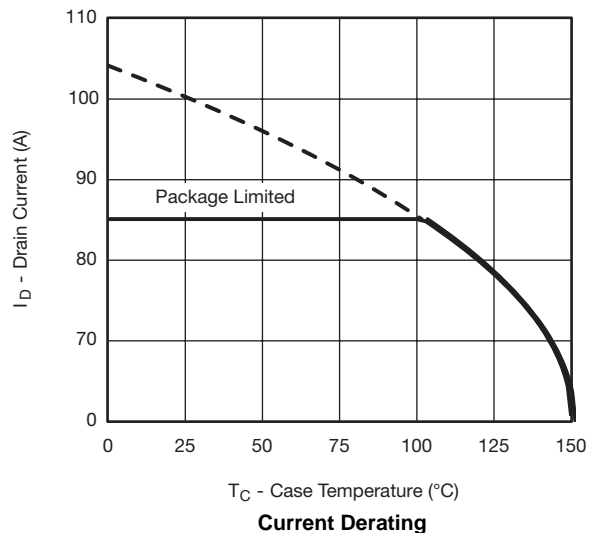
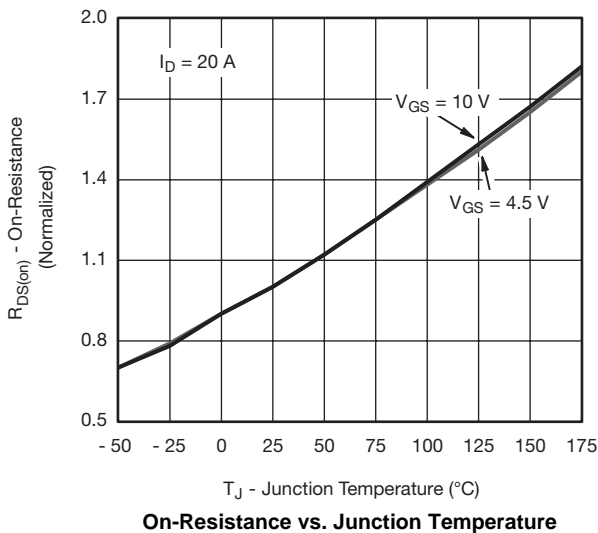
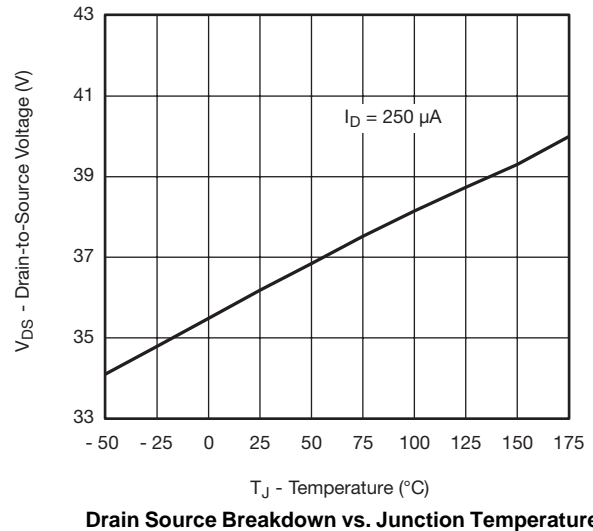
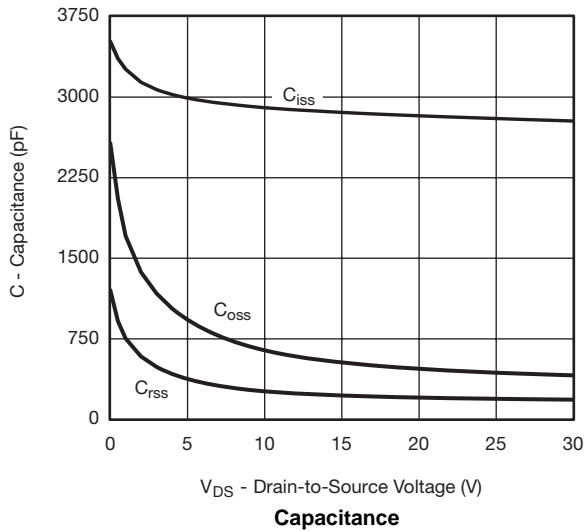
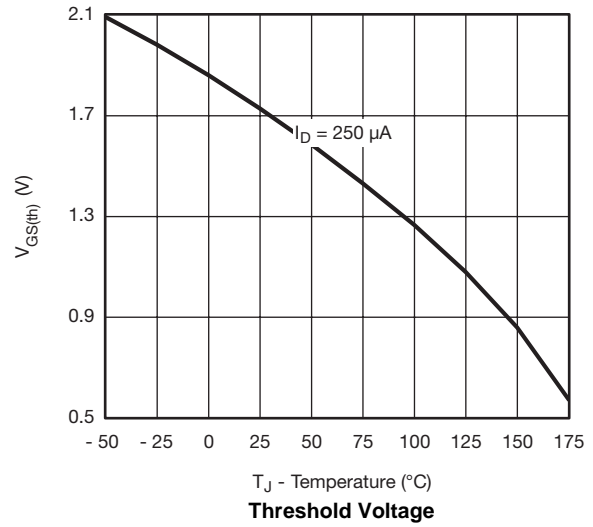
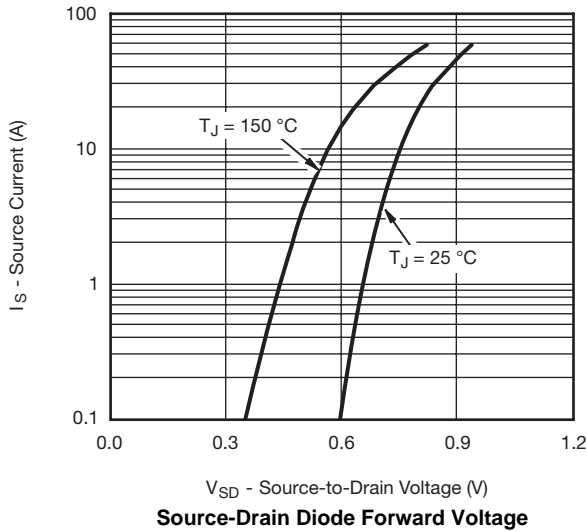


Transconductance

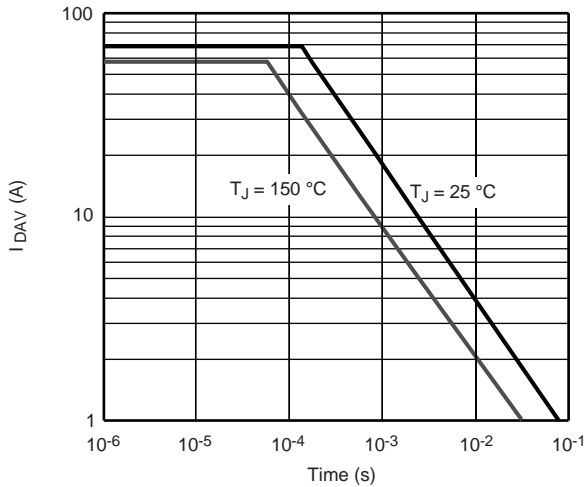


Gate Charge

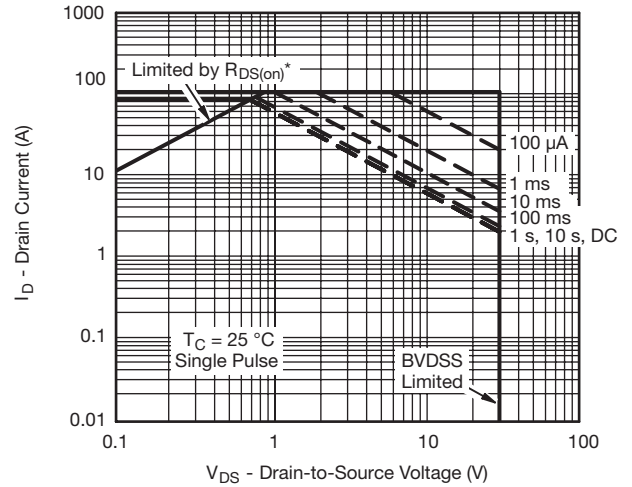
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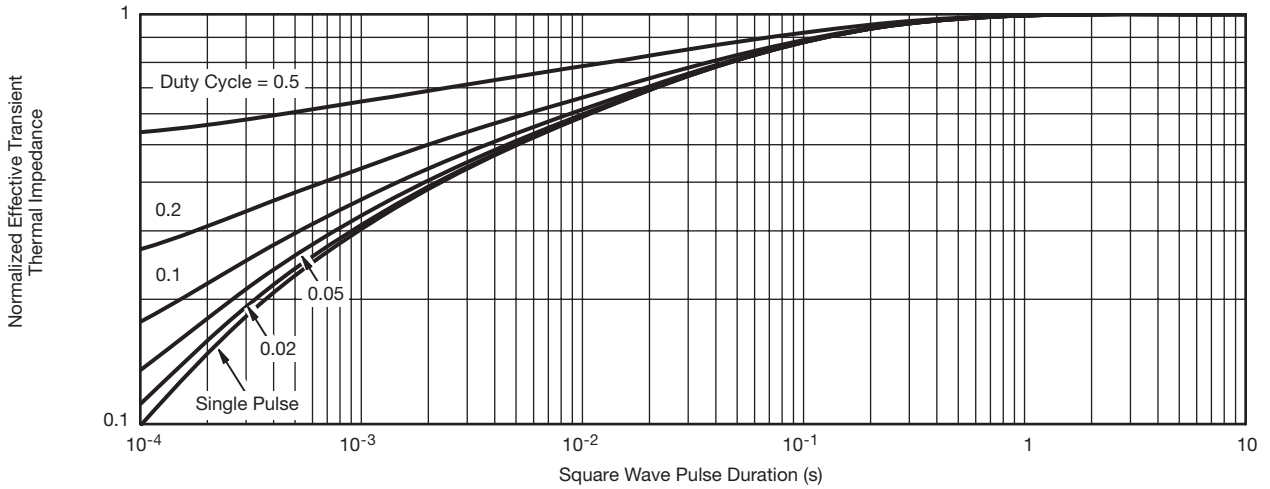
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Single Pulse Avalanche Current Capability vs. Time

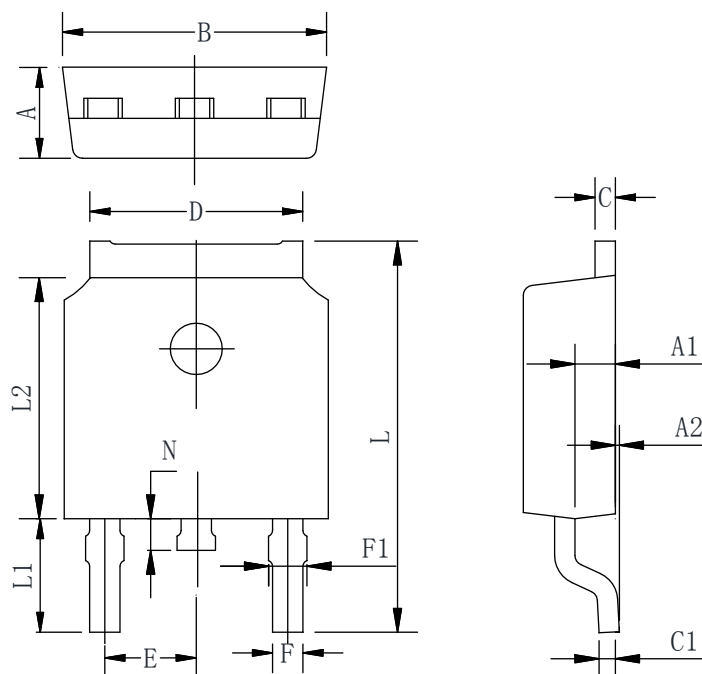


Safe Operating Area
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Case

TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Typ	Max
A	2.10	2.30	2.50
A1	0.88	1.01	1.16
A2	0.00	0.15	0.28
B	6.40	6.60	6.80
C	0.42	0.50	0.63
C1	0.42	0.50	0.63
D	5.08	5.32	5.65
E	2.286 TYP		
F	0.63	0.76	0.89
F1	0.64	0.86	1.08
L	9.30	9.90	10.80
L1	2.4	2.8	3.6
L2	5.90	6.10	6.55
N	0.57	0.80	1.05

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